**CCE201: Solid State Electronic Devices** 

## Lecture 01: Introduction

## Prepared By Dr. Eng. Sherif Hekal Assistant Professor, CCE department

10/20/2018 1



**CCE201** 

#### **Course Information**

**Course Name: Solid State Electronic Devices** 

**Course Code: CCE201** 

Course Materials are on my website:

http://www.bu.edu.eg/staff/sherifsalah3



#### Contact me



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Lecture 01



## My rules

No eating
No drinking
Silence except for asking questions
Shutdown your Mobile, Tablet, etc. and put in your pocket.



### Course meeting time & Location

		Number	Day	Time	Location
		/ week			
Contact hours	lectures	2 h	Saturday	09:00-11:00	Room ??
	tutorial	2 h	Saturday	11:00-13:00	Room ??

Lecture 01



## CCE201: Course Info

Course Title	Solid State Electronic Devices						
Course Code	CCE201						
Credit Hours	3						
<b>Contact Hours</b>	Lecture	2	Tutorials	2	Lab.	-	
Prerequisite(s)	EMP104						
Topics	Basics of semiconductor physics – Fermi-Dirac distribution – Carriers concentrations						
	- Intrinsic and Extrinsic materials - Charge neutrality - Currents in Semiconductors						
	(drift current – diffusion current) – Semiconductor parameters (mobility, Scattering,						
	lifetime) – Hall effect. – PN junction theory – Diode IV characteristics – large and						
	small analysis – Analog and digital diode applications (Rectifiers, Clipping circuits,						
	Clamping Circuits, multipliers) – Special purpose diodes (Light emitting diodes, photo						
	diodes, Zener diode and its applications)- Basics of Bipolar junction transistors (BJT)						
Lecture 01	and field effect transistors (FET) - physical operations, characteristics, specifications.						

#### CCE201

### Course Assessment

Assessment Type	Percentage	Time
Midterm1	30%	Week 07
Midterm2	20%	Week 12
Attendance, Assignments	10%	
Final Exam	40%	Week 16
Total mark	100%	

**Conditions of the success are:** 

- 1- getting 60% of the total mark.
- 2- getting at least 30% of the full mark of the final exam.

Lecture 01



### Course Assessment

Percentage	Grade	Points
Score $\geq 97\%$	A+	4
$93\% \le \text{Score} < 97\%$	А	4
$89\% \le \text{Score} < 93\%$	A-	3.7
$84\% \le Score < 89\%$	B+	3.3
$80\% \leq \text{Score} < 84\%$	В	3
$76\% \leq \text{Score} < 80\%$	В-	2.7
$73\% \le \text{Score} < 76\%$	C+	2.3
$70\% \leq \text{Score} < 73\%$	С	2
$67\% \leq \text{Score} < 70\%$	C-	1.7
$64\% \leq \text{Score} < 67\%$	D+	1.3
$60\% \le \text{Score} < 64\%$	D	1
Score < 60%	F	0
		10/20/20

Lecture 01



# Syllabus

Weeks	Topics			
1	Introduction			
2	Basics of semiconductor physics			
3	Intrinsic & Extrinsic semiconductors			
4	Carrier Transfer			
5	PN-junction			
6	PN-diodes and their applications			
7	Midterm 1			
8	Special purpose diodes			
9	Bipolar junction transistor (BJT) I			
10	Bipolar junction transistor (BJT) II			
11	Bipolar junction transistor (BJT) III			
12	Midterm 2			
13	FET transistor I			
14	FET transistor II			
15	Revision			
Lecture 01	10/20/2018			



# Syllabus

**Text Book** 

S. M. Sze (2001). Semiconductor Devices: Physics and Technology, Wiley & So., ISBN 0471333727.

**Recommended references supporting the course** 

B. Streetman, S. Banerjee (1999).Solid State Electronic Devices, Prentice Hall, ISBN 0130255386.

Robert L. Boylestad, Louis Nashelsky, (2013) **Electronic devices and circuit theory**, 11th edition, Pearson Education

Neamen D.A., (2007), Microelectronics Circuit Analysis and Design, McGraw Hill.

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## Simulators Proteus OrCAD SPICE **Online simulator** http://www.falstad.com/circuit/index.html

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## ILOS

- Theory
- Analysis
- Simulation
- Implementation

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## ILOS

#### Upon successful completion of the course, students will be able to:

- Acquire some understanding in the fundamental electric and electronics principles.
- Describe the operation and i-v characteristics of diodes and transistors.
- Solve basic problems in electronic circuits.
- Implement different applications using basic electronic devices (diodes and transistors).
- Read and understand the datasheets of diodes and transistors to use the suitable parts in design.
- Design and analyze electronic circuits use computer packages (simulators).

Acquire better skills in performing the laboratory experiments.

Work as a team in laboratory sessions.

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## Course Objectives

- Identify and describe operation of semiconductor devices through understanding of the semiconductor physics.
- Develop an understanding of the PN junction diode and its behavior.
- Develop an ability to analyze diode circuits and examine additional applications of the diode.
- Develop an understanding of the Bipolar Junction Transistor (BJT) and its operation.
- Identify and describe the different BJT configurations, DC biasing, and AC analysis.
- Develop an understanding of the Field Effect Transistor (FET) and its operation.
- Identify and describe the different FET configurations, DC biasing, and AC analysis.
- Develop an ability to analyze and design BJT and FET circuits.

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Course Objectives



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## Course Objectives







#### **CCE201**

State two (2) differences between FET and BJT – LEVEL 1

Explain how depletion region is created in a pn junction? – LEVEL 2

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Sketch the output voltage, V<sub>O</sub> if the input signal, V<sub>i</sub> is a 12 V peak-to-peak square wave – LEVEL 3

Analyze the circuit below to calculate the base, collector and emitter currents – LEVEL 4

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• Compare the two characteristics for a conventional pn-junction diode and a Zener diode – LEVEL 4/5

 Evaluate the circuit below to determine whether the BJT is in cut-off, active or saturation mode – LEVEL
 5

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Design an n-channel MOSFET circuit is as shown in the figure - LEVEL 6

#### NOTE:

A <u>DESIGN</u> question generally means that you are required to calculate the values of the resistors.



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